

P-Channel Enhancement Mode Power MOSFET

Description

The HM2P20Q uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = -200V, I_D = -2A$
 $R_{DS(ON)} < 1500m\Omega @ V_{GS} = -10V$ (Typ. = 1250mR)

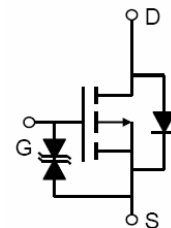
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

Application

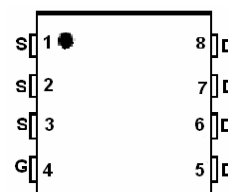
- Portable equipment and battery powered systems

100% UIS TESTED!

100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM2P20Q	HM2P20Q	DFN3X3-8L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-200	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-2	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	-1.4	A
Pulsed Drain Current	I_{DM}	-6	A
Maximum Power Dissipation	P_D	160	W
Derating factor		1.3	W/ $^\circ C$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta jc}$	0.8	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

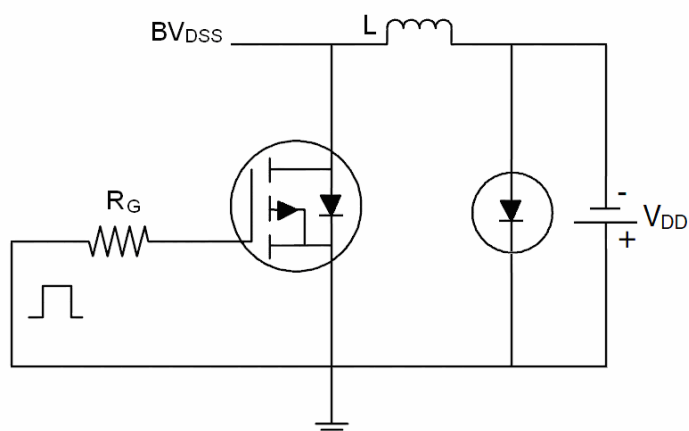
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-145	-155	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-145V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-4	-	-2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	1250	1500	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-20A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-75V, V _{GS} =0V, F=1.0MHz	-	7650	-	PF
Output Capacitance	C _{oss}		-	148	-	PF
Reverse Transfer Capacitance	C _{rss}		-	131	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-75V, I _D =-20A V _{GS} =-10V, R _{GEN} =9.1Ω	-	17	-	nS
Turn-on Rise Time	t _r		-	80	-	nS
Turn-Off Delay Time	t _{d(off)}		-	45	-	nS
Turn-Off Fall Time	t _f		-	65	-	nS
Total Gate Charge	Q _g	V _{DS} =-75V, I _D =-20A, V _{GS} =-10V	-	137	-	nC
Gate-Source Charge	Q _{gs}		-	25	-	nC
Gate-Drain Charge	Q _{gd}		-	28	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-11A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S	-	-	-	-2	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-11A di/dt = 100A/μs (Note3)	-	90	-	nS
Reverse Recovery Charge	Q _{rr}		-	105	-	nC

Notes:

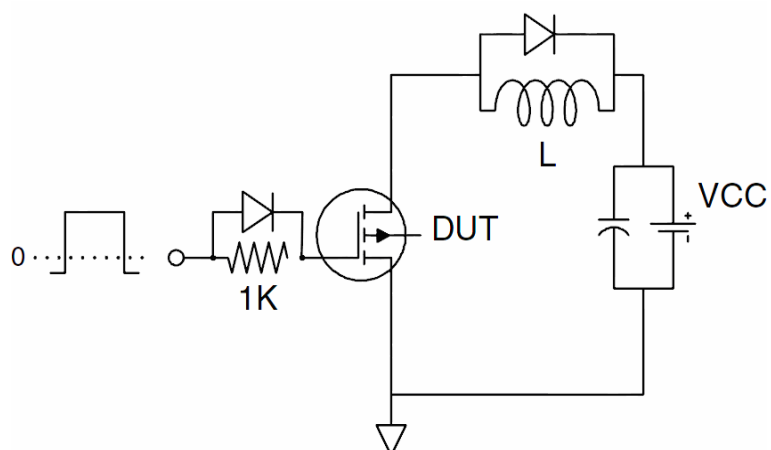
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=-75V, V_G=-10V, L=0.5mH, R_g=25\Omega$

Test Circuit

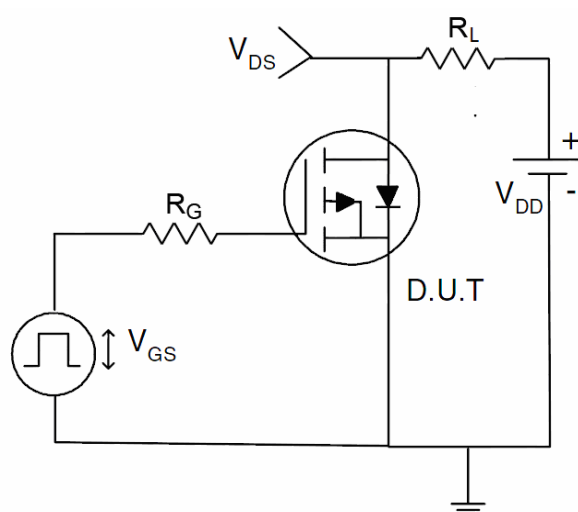
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

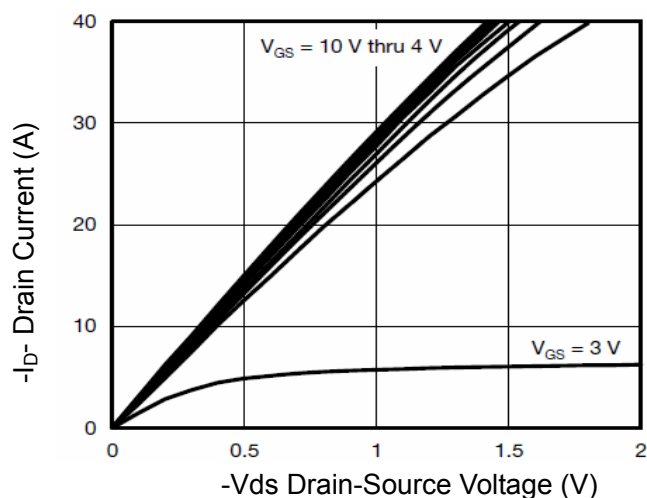


Figure 1 Output Characteristics

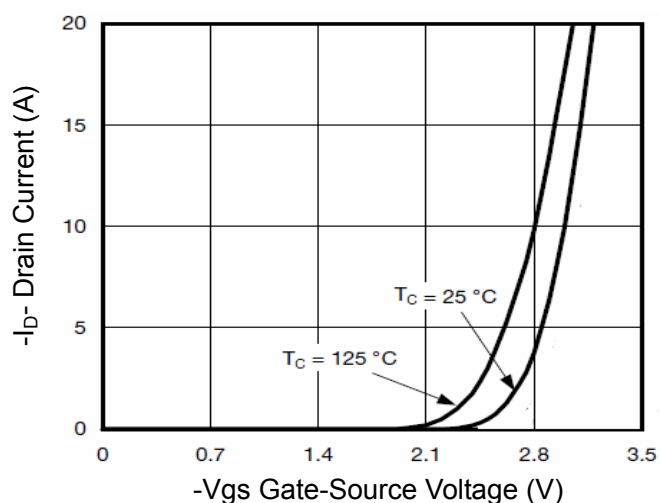


Figure 2 Transfer Characteristics

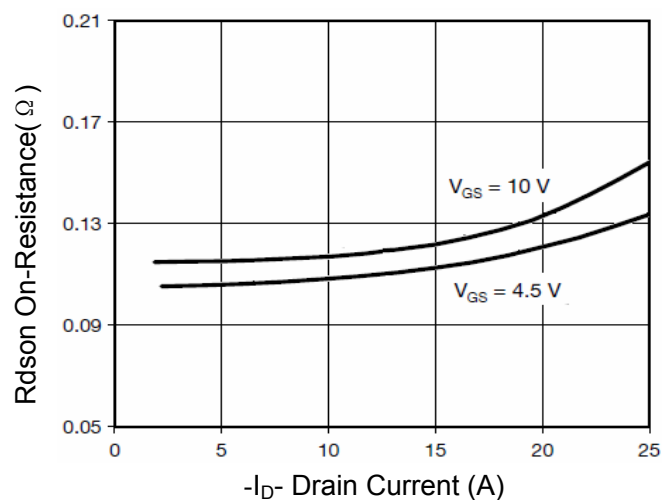


Figure 3 $R_{DS(on)}$ - Drain Current

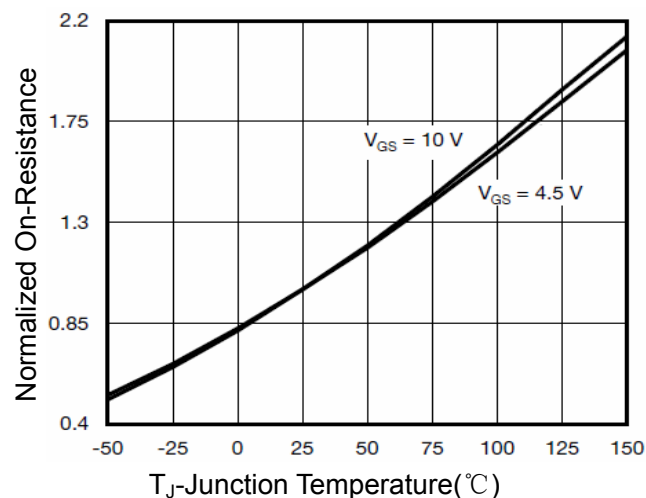


Figure 4 $R_{DS(on)}$ -Junction Temperature

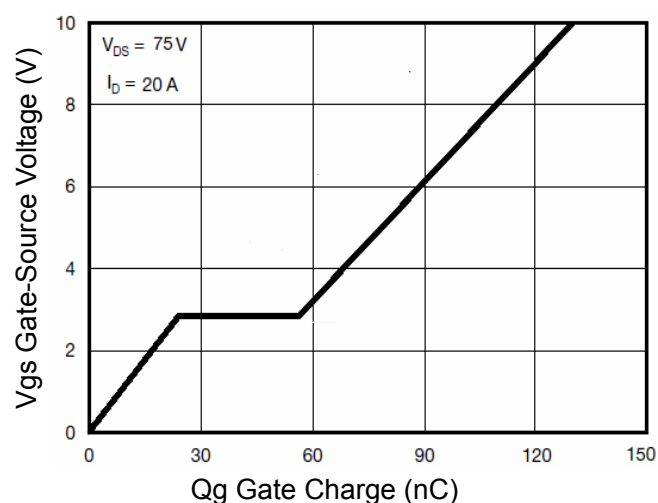


Figure 5 Gate Charge

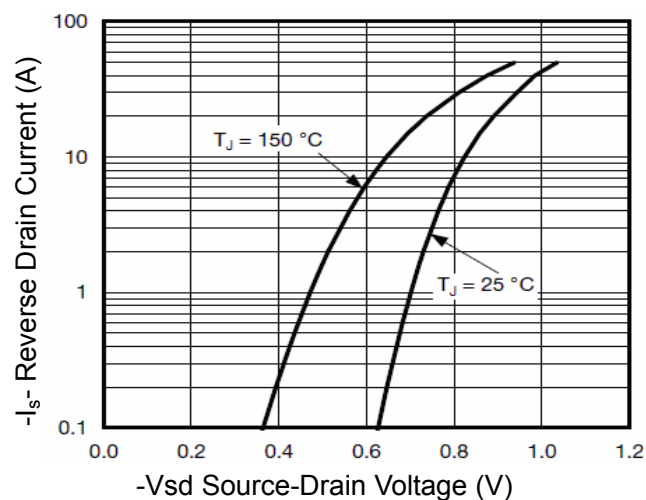


Figure 6 Source- Drain Diode Forward

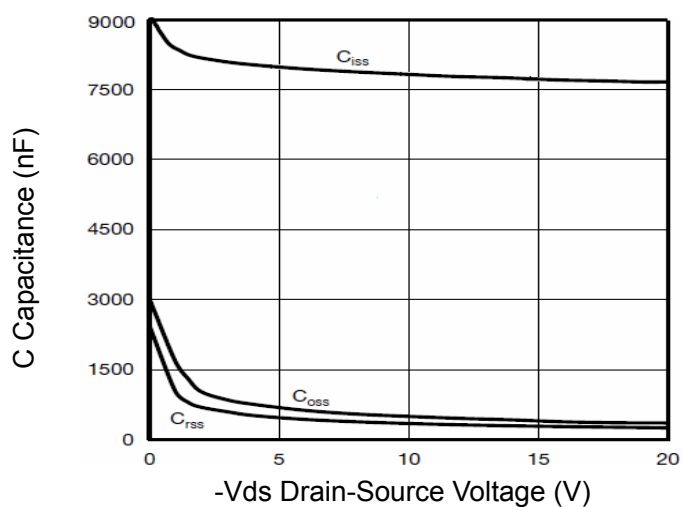


Figure 7 Capacitance vs Vds

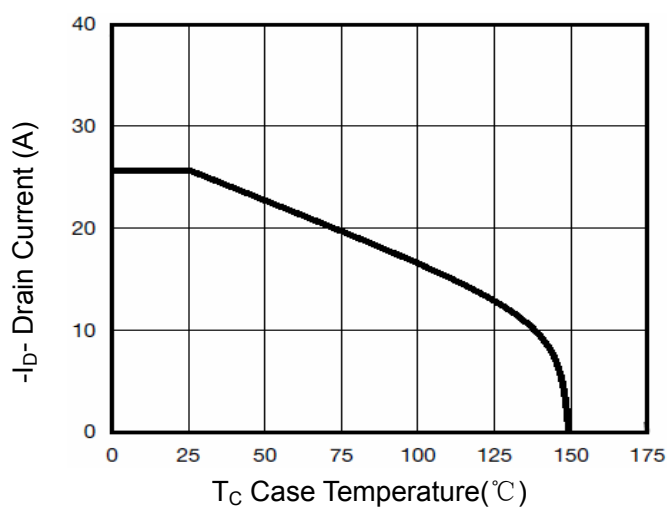


Figure 9 Drain Current vs Case Temperature

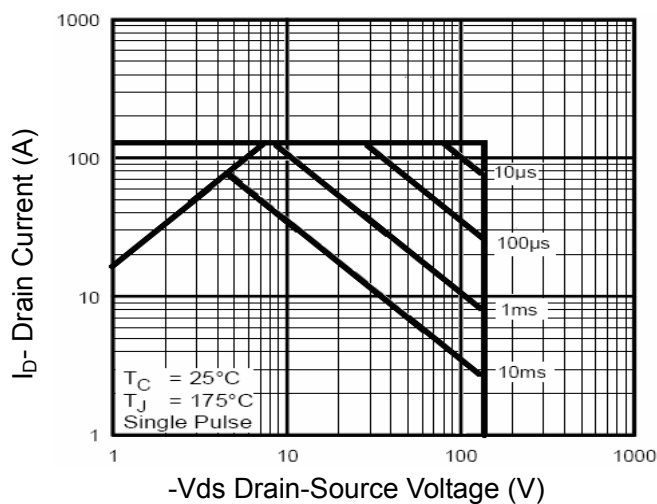


Figure 8 Safe Operation Area

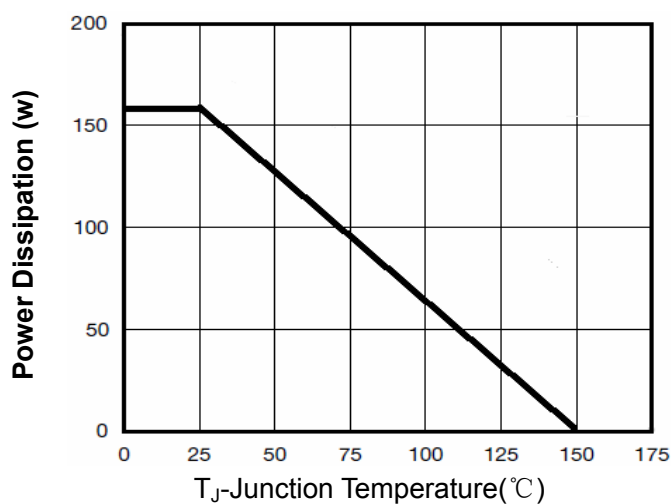


Figure 10 Power De-rating

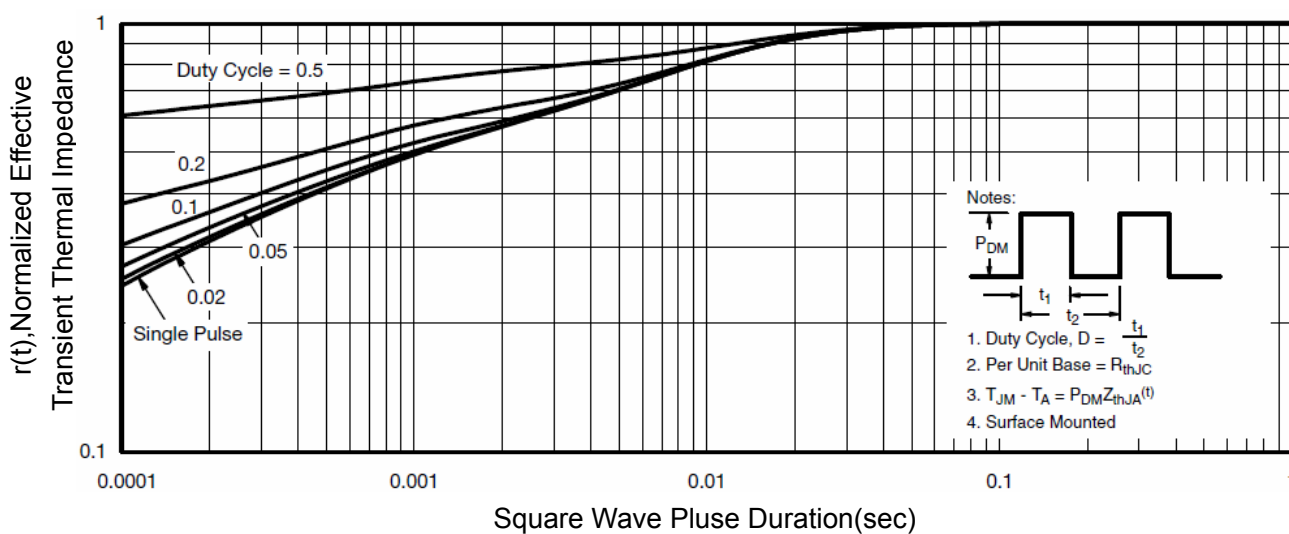
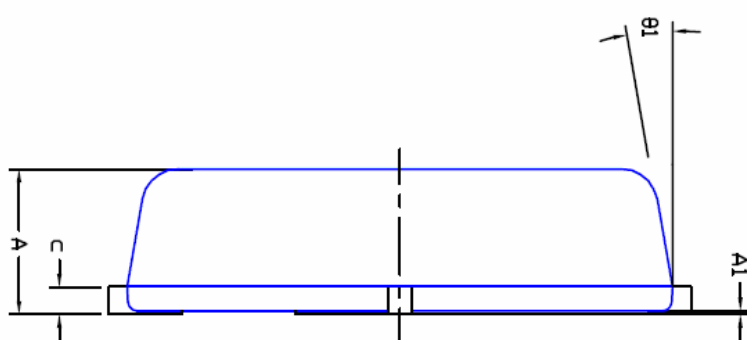
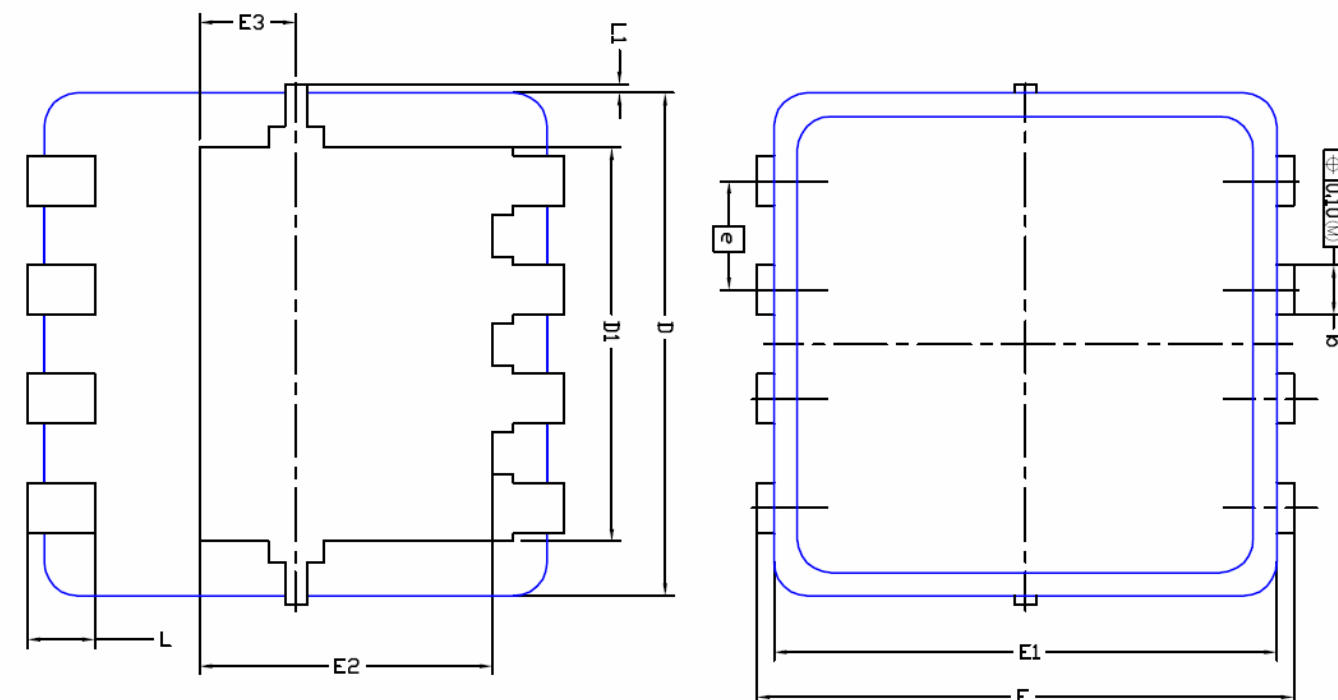


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3X3 EP Package Information



DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.05	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0118	0.0157	0.0197
L1	0	---	0.100	0	---	0.004
θ1	0°	10°	12°	0°	10°	12°